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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/526,564	03/04/2005	Takumi Yamaguchi	67471-065	9368

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EXAMINER

LIU, BENJAMIN T

ART UNIT	PAPER NUMBER
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2826

DATE MAILED: 09/28/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No. 10/526,564	Applicant(s) YAMAGUCHI, TAKUMI	
	Examiner Benjamin T. Liu	Art Unit 2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.


- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 08 June 2006.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-14 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-14 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.


Minhloan Tran
Primary Examiner
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Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-5 and 10-11 are rejected under 35 U.S.C 103(a) as being unpatentable over Yuzurihara et al. (EP1075028) in view of Yamasaki (4,870,441).

With regard to claim 1, figures 1 and 11 of Yuzurihara et al. disclose a solid-state imaging apparatus that includes an imaging region 41 and a drive circuit region 42 both formed on one semiconductor substrate, the imaging region 41 including an active-type unit pixel 41' in which a photodiode unit 1 generates signal charge by photoelectric conversion and an amplification unit 5 amplifies the signal charge, the drive circuit region 42 being for driving the photodiode unit 1 and the amplification unit 5, the imaging region 41 and the drive circuit region 42 including one or more transistors respectively, wherein the transistors in the imaging region 41 and the drive circuit region 42 have a same channel polarity. (Note lines 1-2 in paragraph [0076] of Yuzurihara et al.)

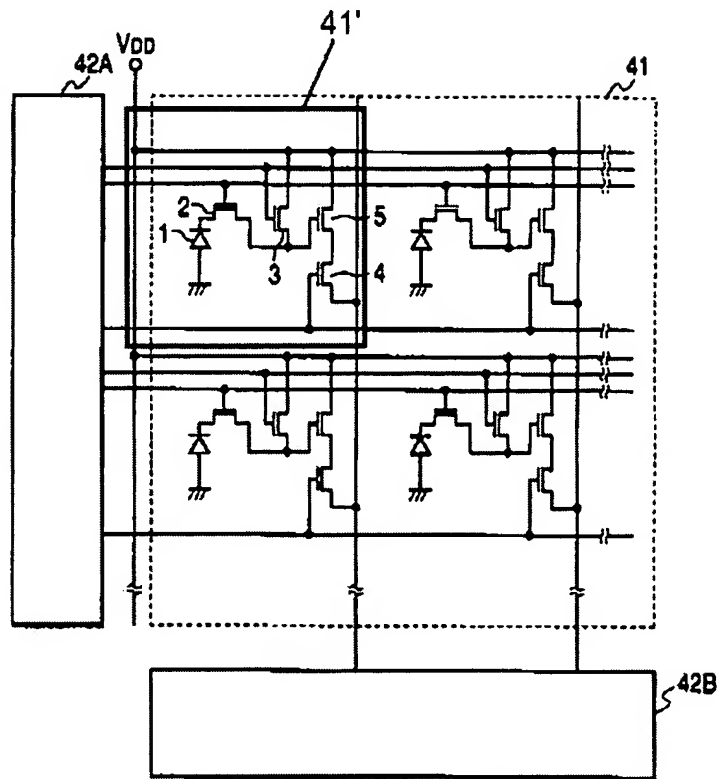


Figure 1: solid-state imaging apparatus with pixel 41'

Figures 1 and 11 of Yuzuihara et al. does not discloses all the transistors in the imaging region and the drive circuit region have a same channel polarity.

However, figure 3 of Yamasaki discloses all the transistors in the imaging region ($Q_6 - Q_{10}$) and the drive circuit region ($Q_1 - Q_5$) have a same channel polarity. (Note lines 63-65 in column 3 of Yamasaki)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. with the transistors of Yamasaki in order to decrease the number of process required for forming all the transistors,

decrease the leakage current, decrease the noise during driving operations, and increase the image quality.

With regard to claim 2, figures 1 and 11 of Yuzurihara et al. disclose all the subject matter claimed except for the transistors being of an n-channel MOS type.

However, figure 3 of Yamasaki discloses the transistors ($Q_1 - Q_{10}$) being of an n-channel MOS type. (Note lines 63-65 in column 3 of Yamasaki)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. with the transistors of Yamasaki in order to decrease the number of process required for forming all the transistors, decrease the leakage current, decrease the noise during driving operations, and increase the image quality.

With regard to claim 3, figures 1, 11, and 12 of Yuzurihara et al. disclose a solid-state imaging apparatus, wherein the drive circuit region 42 includes a dynamic circuit that includes a capacitor 7 for accumulating electric charge and a transistor 11 for performing a switching function.

With regard to claim 4, figures 1, 11, and 12 of Yuzurihara et al. disclose a solid-state imaging apparatus, wherein the imaging region 41 includes a plurality of active-type unit pixels 41', and the drive circuit region 42 includes a pixel selection circuit (42A, 42B) for selecting, one active-type unit pixel 41' from the plurality of active-type unit pixels and a shift resistor circuit for outputting a selection instruction signal to the pixel selection circuit (42A, 42B). (Note lines 5-11 in paragraph [0118] of Yuzurihara et al.)

With regard to claim 5, figures 1, 11, and 12 of Yuzurihara et al. disclose a solid-state imaging apparatus, wherein the imaging region 41 includes a transistor 4 for performing a switching function based on a signal received from the drive circuit region 42, and the signal charge is output to the amplification unit 5 while the transistor 4 for performing the switching function is ON.

With regard to claim 10, figures 1 and 11 of Yuzurihara et al. disclose a manufacturing method for a solid-state imaging apparatus, comprising steps of: forming, on a semiconductor substrate 21, an imaging region 41 including a photodiode unit 1 for converting input light into signal charge and an amplification unit 5 for amplifying the signal charge; and forming, on the semiconductor substrate 21, a drive circuit region 42 for driving the imaging region 41, wherein MOS type transistors having a same channel polarity are formed in both steps for forming the imaging region 41 and the drive circuit region 42 respectively. (Note lines 1-2 in paragraph [0076] of Yuzurihara et al.)

Figures 1 and 11 of Yuzurihara et al. does not disclose all transistors formed in both steps for forming the imaging region and the drive circuit region respectively are MOS type transistors having a same channel polarity.

However, figure 3 of Yamasaki discloses all transistors formed in both steps for forming the imaging region ($Q_6 - Q_{10}$) and the drive circuit region ($Q_1 - Q_5$) respectively are MOS type transistors having a same channel polarity. (Note lines 63-65 in column 3 of Yamasaki)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. with the transistors of Yamasaki in

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order to decrease the number of process required for forming all the transistors, decrease the leakage current, decrease the noise during driving operations, and increase the image quality.

With regard to claim 11, figures 1 and 11 of Yuzurihara et al. disclose all the subject matter claimed except for the MOS type transistors formed in both steps being of n-channel MOS type.

However, figure 3 of Yamasaki discloses the MOS type transistors ($Q_1 - Q_{10}$) formed in both steps being of n-channel MOS type. (Note lines 63-65 in column 3 of Yamasaki)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. with the transistors of Yamasaki in order to decrease the number of process required for forming all the transistors, decrease the leakage current, decrease the noise during driving operations, and increase the image quality.

Claims 6-8 and 12-14 are rejected under 35 U.S.C 103(a) as being unpatentable over Yuzurihara et al. (EP 1075028) in view of Yamasaki (4,870,441) and further in view of Momose et al. (6,642,560).

With regard to claim 6, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a transistor of a MOS type, of which a gate length is equal to or less than 0.6 μm .

However, figure 1 of Momose et al. discloses a transistor of a MOS type, of which a gate length is .3um, which is less than .6um. (Note line 10 in the abstract of Momose et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors at the gate lengths taught by Momose et al. in order to decrease the size of each MOS transistor.

With regard to claim 7, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a transistor of a MOS type, of which a film thickness of a gate insulator is in a range from 1 nm to 20 nm.

However, figure 1 of Momose et al. discloses a transistor of a MOS type, of which a film thickness of a gate insulator is less than 2.5nm, which is within the range of 1nm to 20nm. (Note lines 6-7 in the abstract of Momose et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors of Momose et al. in order to maintain a certain threshold voltage in each transistor.

With regard to claim 8, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a transistor of a MOS type, an insulator that has a film thickness in a range from 1 nm to 20 nm and functions as a capacitor, which is formed between a gate electrode of the transistor and the semiconductor substrate.

However, figure 1 of Momose et al. discloses a transistor of a MOS type, an insulator 3 that has a film thickness of less than 2.5nm, which is in a range from 1nm to

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20nm, and which functions as a capacitor, which is formed between a gate electrode 2 of the transistor and the semiconductor substrate 1. (Note lines 6-7 in the abstract of Momose et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors of Momose et al. in order to maintain a certain threshold voltage in each transistor.

With regard to claim 12, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a solid-state imaging apparatus, wherein a gate length of each MOS type transistor is equal to or less than 0.6 μm .

However, figure 1 of Momose et al. discloses a MOS type transistor, wherein a gate length is .3 μm , which is less than .6 μm . (Note line 10 in the abstract of Momose et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors of Momose et al. in order to create a solid-state imaging apparatus with small transistors.

With regard to claim 13, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a solid-state imaging apparatus, wherein a film thickness of a gate insulator in each MOS type transistor is in a range from 1 nm to 20 nm.

However, figure 1 of Momose et al. discloses a transistor, wherein a film thickness of a gate insulator in each MOS type transistor is less than 2.5 nm, which is in a range from 1 nm to 20 nm. (Note lines 6-7 in the abstract of Momose et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors of Momose et al. in order to form the solid-state imaging apparatus with transistors that have a certain threshold voltage.

With regard to claim 14, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a solid-state imaging apparatus, wherein an insulator that has a film thickness in a range from 1 nm to 20 nm, and functions as a capacitor is formed between a gate electrode of each MOS type transistor and the semiconductor substrate.

However, figure 1 of Momose et al. discloses a transistor, wherein an insulator that has a film thickness of less than 2.5 nm, which is in a range from 1 nm to 20 nm, and functions as a capacitor is formed between a gate electrode 2 of each MOS type transistor and the semiconductor substrate 1.

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki with the transistors of Momose et al. in order to form solid-state imaging apparatus with transistors that have a certain threshold voltage.

Claim 9 is rejected under 35 U.S.C 103(a) as being unpatentable over Yuzurihara et al. (EP 1075028) in view of Yamasaki (4,870,441) and further in view of Shinohara et al. (5,698,844).

With regard to claim 9, Yuzurihara et al. and Yamasaki disclose all the subject matter claimed except for a camera that includes the solid-state imaging apparatus.

However, figure 1 of Shinohara et al. discloses a solid-state imaging apparatus that is included in a camera. (Note lines 9-10 in column 1 of Shinohara et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the solid-state imaging apparatus of Yuzurihara et al. and Yamasaki inside the camera of Shinohara et al. in order to be used as the line sensor for an image scanner and an area sensor for the camera.

Conclusion

2. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Benjamin T. Liu whose telephone number is (571) 272-6009. The examiner can normally be reached on Mon-Fri 9:30 AM-6:00AM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on 571 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BTL
8/17/2006